



6-Pin DIP Random-Phase Optoisolators Triac Driver Output (250 Volts Peak)

The MOC3010 Series consists of gallium arsenide infrared emitting diodes, optically coupled to silicon bilateral switch and are designed for applications requiring isolated triac triggering, low–current isolated ac switching, high electrical isolation (to 7500 Vac peak), high detector standoff voltage, small size, and low cost.

• To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

Recommended for 115 Vac(rms) Applications:

- Solenoid/Valve Controls
- Lamp Ballasts
- Interfacing Microprocessors to 115 Vac Peripherals
- Motor Controls
- Static ac Power Switch
- Solid State Relays
- Incandescent Lamp Dimmers

Storage Temperature Range

Soldering Temperature (10 s)

MAXIMUM RATINGS (T_A = 25° C unless otherwise noted)

V _R I _F P _D	3 60 100 1.33	Volts mA mW mW/°C
١ _F	60 100	mA mW
•	100	mW
PD		
	1.33	mvv/°C
VDRM	250	Volts
ITSM	1	A
PD	300 4	mW mW/°C
V _{ISO} 7500		Vac(pk)
P _D 330 4.4		mW mW/°C
ТJ	-40 to +100	°C
T۸	-40 to +85	°C
_	ITSM PD VISO PD TJ	ITSM 1 PD 300 4 VISO 7500 PD 330 4.4 TJ -40 to +100

T_{sta}

ΤL

-40 to +150

260

°C

°C

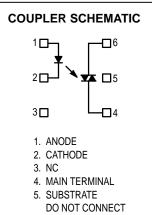
ng, high ge, small quirements, the is a test option.

STANDARD THRU HOLE

MOC3010

MOC3011

MOC3012



6. MAIN TERMINAL

 Isolation surge voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.



MOC3010, MOC3011, MOC3012

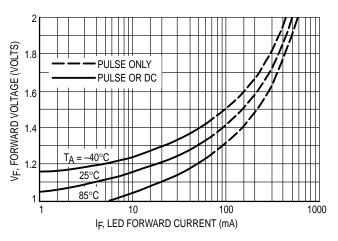
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
INPUT LED						
Reverse Leakage Current (V _R = 3 V)		۱ _R	—	0.05	100	μΑ
Forward Voltage (I _F = 10 mA)		۷ _F	—	1.15	1.5	Volts
OUTPUT DETECTOR (I _F = 0 unless otherwise noted)						•
Peak Blocking Current, Either Direction (Rated V _{DRM} ⁽¹⁾)		^I DRM	—	10	100	nA
Peak On–State Voltage, Either Direction (I _{TM} = 100 mA Peak)		VTM	—	1.8	3	Volts
Critical Rate of Rise of Off-State Voltage (Figure 7, Note 2))	dv/dt	—	10	—	V/µs
COUPLED		•				
M	DC3010 DC3011 DC3012	IFT		8 5 3	15 10 5	mA
Holding Current, Either Direction		ŀн	_	100	—	μΑ

1. Test voltage must be applied within dv/dt rating.

2. This is static dv/dt. See Figure 7 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.

3. All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT}. Therefore, recommended operating I_F lies between max I_{FT} (15 mA for MOC3010, 10 mA for MOC3011, 5 mA for MOC3012) and absolute max I_F (60 mA).



TYPICAL ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C$

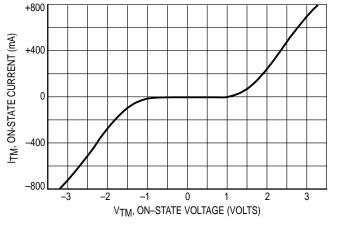


Figure 1. LED Forward Voltage versus Forward Current

Figure 2. On–State Characteristics

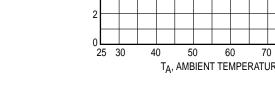
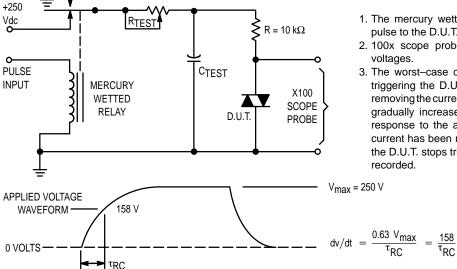
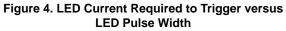


Figure 5. dv/dt versus Temperature



- 1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
- 2. 100x scope probes are used, to allow high speeds and voltages.
- 3. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable RTEST allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. τ_{RC} is measured at this point and recorded.



IFT, NORMALIZED LED TRIGGER CURRENT 5 0 80 2 100 5 10 20 PWin, LED TRIGGER WIDTH (µs)

STATIC dv/dt

CIRCUIT IN FIGURE 6

25

20

15

10

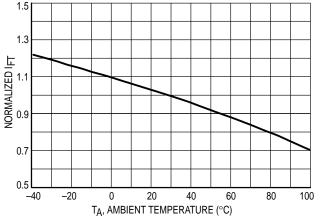


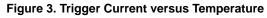
NORMALIZED TO:

 $PW_{in} \ge 100 \,\mu s$

50

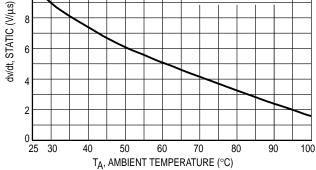
100



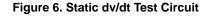


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FAIRCHILD SEMICONDUCTOR





MOC3010, MOC3011, MOC3012

TYPICAL APPLICATION CIRCUITS

NOTE: This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only. Additional information on the use of the MOC3010/3011/3012 is available in Application Note AN–780A.

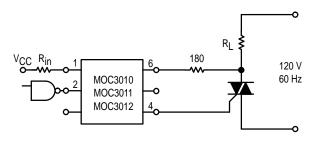


Figure 7. Resistive Load

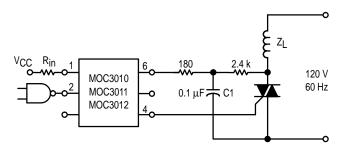


Figure 8. Inductive Load with Sensitive Gate Triac (IGT $\,\leqslant\,$ 15 mA)

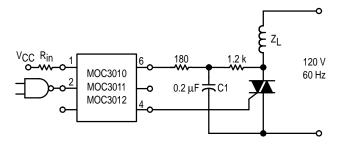
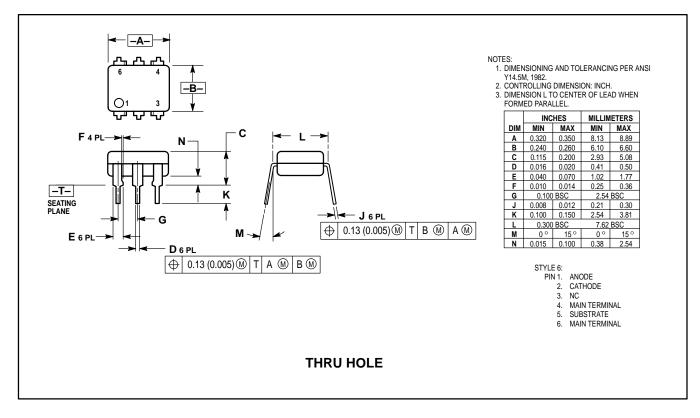


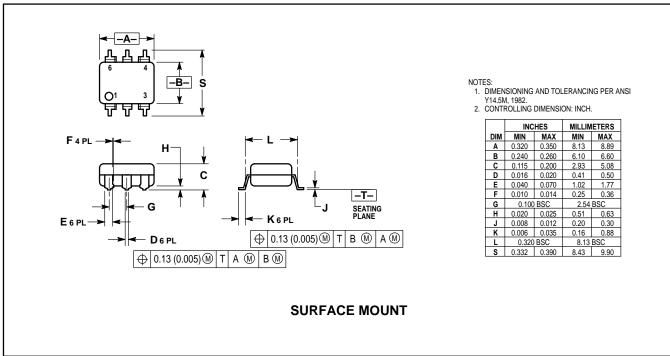
Figure 9. Inductive Load with Non–Sensitive Gate Triac (15 mA < IGT < 50 mA)



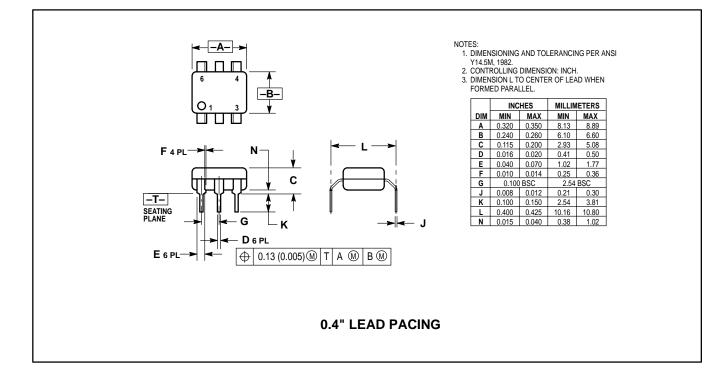
MOC3010, MOC3011, MOC3012

PACKAGE DIMENSIONS











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